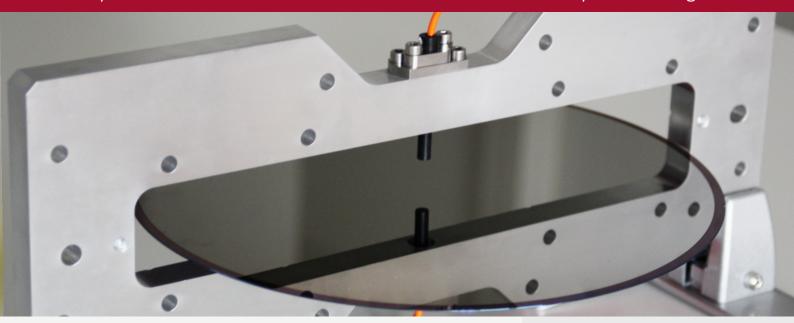


EddyCus® inline ICM – Interconnection Module for Quality Monitoring P_CM_22



Highlights

- ► Non-contact and non-destructive
- ► Near-process monitoring
- ▶ High-speed and accurate
- ► High repeatability and long term stability
- ► Test directly on product wafers
- ► Easy integration into tools

Sensor Series

- ► Sheet resistance (Ohm/sq)
- ► Resistivity (mOhm·cm)
- Metal layer thickness (nm, μm)
- Metal substrate thickness (μm)
- ► Uniformity / homogeneity
- ▶ Defects and effects

SURAGUS GmbH Maria-Reiche-Strasse 1 01109 Dresden

Germany

For further questions:

+49 351 32 111 520

sales@suragus.com

Visit us at:

www.suragus.com

www.suragus.com/calculator

www.suragus.com/EddyCusNearProcess

Applications

- ▶ Wafer testing
- ▶ Thin film layer characterization
- ► Material characterization
- Imaging and mapping
- ► Defect detection
- ▶ Integrity assessment
- ► Material sorting
- ► Sputter target wear level monitoring

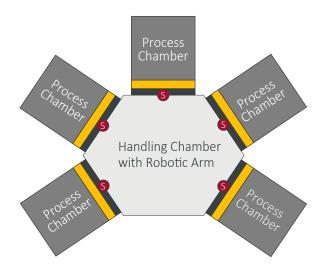
Materials

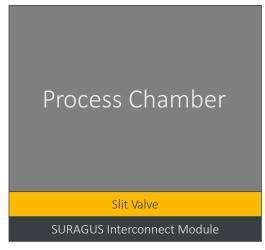
- Semiconductors
- ► Si (mono, ply)
- ▶ WBG SiC, SiSiC, GaN
- ► GaAs, GaP, InP, GaAsP etc
- Metals
- Alloys
- ► Graphite
- Graphene
- ► Compounds
- Composites

Engineered and Made in Germany











Measurement technology	Non-contact high frequency eddy current sensor
Place of measurement	In-vacuo installation between handling area and slit valve
Substrates	Wafer, glass etc.
Measurement gap size	5 – 50 mm (depending on wafer handler)
Module sizes	150 / 200 / 300 mm
Conductive layers	Metals, alloys and other conductive layers
Sheet resistance measurement range	0.01 – 10 Ohm/sq
Thickness measurement of metal films (e.g. Cu, Al, Ag, Au, Ni, Ti, Ta, Pt, W)	5 nm – 2 mm (in accordance with sheet resistance)
Other integrated measurements	Sheet resistance, metal thickness, resistivity, wafer temperature
Environment	Ex-vacuo / in-vacuo @ T up to 220°C / 428°F
Sample rate	1 − 1,000 measurements per second for line scan
Hardware trigger	5 / 12 / 24 V
Interfaces	UDP, .Net libraries, TCP, Modbus, Profinet, analog/digital

Insights gained by near process monitoring

- ▶ Line profile of sheet resistance, metal layer thickness, resistivity
- ▶ Instant deposition data for new material configurations
- ► Measurement directly on process wafers
- ► Wafer-to-wafer and first wafer effects
- ► Chamber-to-Chamber effects
- ► Data for run-to-run control
- ▶ Effects of target lifetime
- ► Smart recipe control

